

N-channel TrenchMOS standard level FET Rev. 02 — 8 July 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC convertors

Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|--|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 100 | V |
| I_D | drain current | $T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V$ | - | - | 47 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | - | - | 150 | W |
| Static chara | acteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$ | - | 22 | 25 | mΩ |
| Dynamic ch | naracteristics | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10 \text{ V}; I_D = 45 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C}$ | - | 25 | - | nC |



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2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | G | gate | | _ |
| 2 | D | drain[1] | mb | D |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | mbb076 S | |
| | | | SOT404 (D2PAK) | |

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| PHB45NQ10T | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 100 | V |
| V_{DGR} | drain-gate voltage | $T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 100 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | $V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}$ | - | 33 | Α |
| | | V _{GS} = 10 V; T _{mb} = 25 °C | - | 47 | Α |
| I _{DM} | peak drain current | pulsed; T _{mb} = 25 °C | - | 188 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | - | 150 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| Source-drai | n diode | | | | |
| Is | source current | T _{mb} = 25 °C | - | 47 | Α |
| I _{SM} | peak source current | pulsed; T _{mb} = 25 °C | - | 188 | Α |
| Avalanche r | uggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 40 A; V_{sup} ≤ 25 V; unclamped; t_p = 100 µs; R_{GS} = 50 Ω | - | 260 | mJ |
| I _{AS} | non-repetitive avalanche current | $V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{ unclamped}$ | - | 47 | Α |

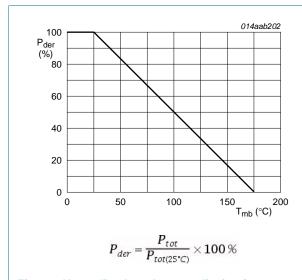


Fig 1. Normalized total power dissipation as a function of mounting base temperature

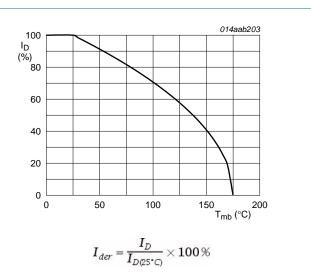


Fig 2. Normalized continuous drain current as a function of mounting base temperature

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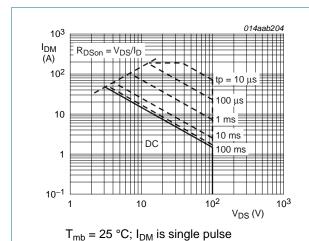


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

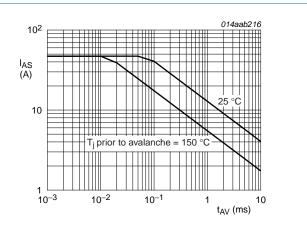


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | | - | - | 1 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | mounted on printed-circuit board; minimum footprint | - | 50 | - | K/W |

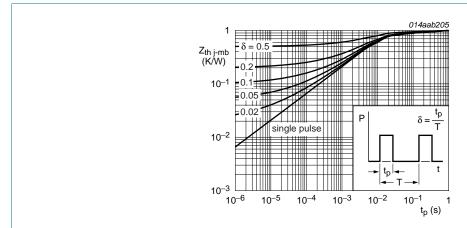


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

| Table 6. | Characteristics | | | | | |
|---|---|--|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 89 | - | - | V | |
| | breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 100 | - | - | V |
| V _{GS(th)} gate-source threshold voltage | gate-source threshold | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$ | - | - | 6 | V |
| | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$ | 1 | - | - | V | |
| | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 2 | 3 | 4 | V | |
| I _{DSS} | drain leakage current | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$ | - | - | 500 | μΑ |
| | | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.05 | 10 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.02 | 100 | nA |
| | | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 100 | nA |
| R _{DSon} | R _{DSon} drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C}$ | - | - | 68 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C | - | 22 | 25 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 61 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 13 | - | nC |
| Q_{GD} | gate-drain charge | | - | 25 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ | - | 2600 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 340 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 195 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 50 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$ | - | 18 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}C$ | - | 72 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 69 | - | ns |
| t _f | fall time | | - | 58 | - | ns |
| L _D | internal drain inductance | from tab to centre of die ; $T_j = 25$ °C | - | 3.5 | - | nΗ |
| L _S | internal source inductance | from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$ | - | 7.5 | - | nΗ |
| Source-di | rain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.87 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; | - | 82 | - | ns |
| Qr | recovered charge | $V_{DS} = 25 \text{ V; } T_j = 25 \text{ °C}$ | - | 0.26 | - | μC |

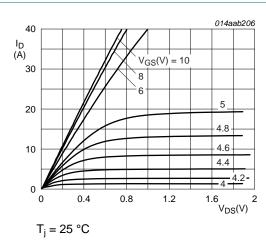


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

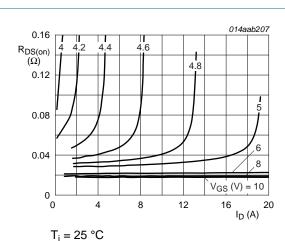


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

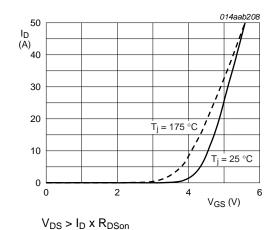


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

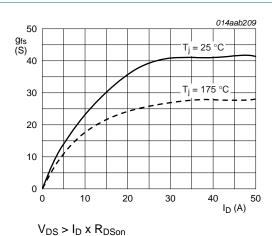


Fig 9. Forward transconductance as a function of drain current; typical values

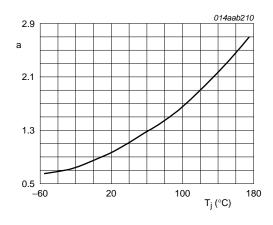


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

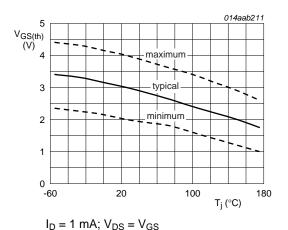


Fig 11. Gate-source threshold voltage as a function of junction temperature

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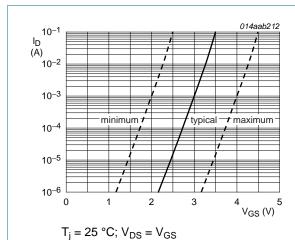
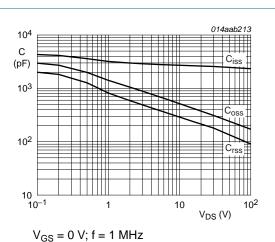
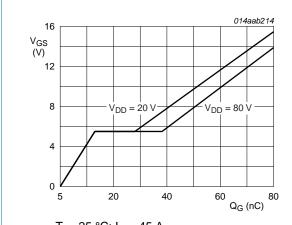


Fig 12. Sub-threshold drain current as a function of gate-source voltage



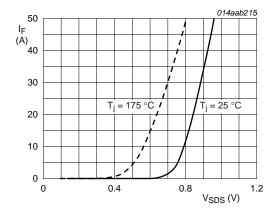
VGS = 0 V, T = 1 WH12

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25 \, ^{\circ}\text{C}; \, I_D = 45 \, \text{A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

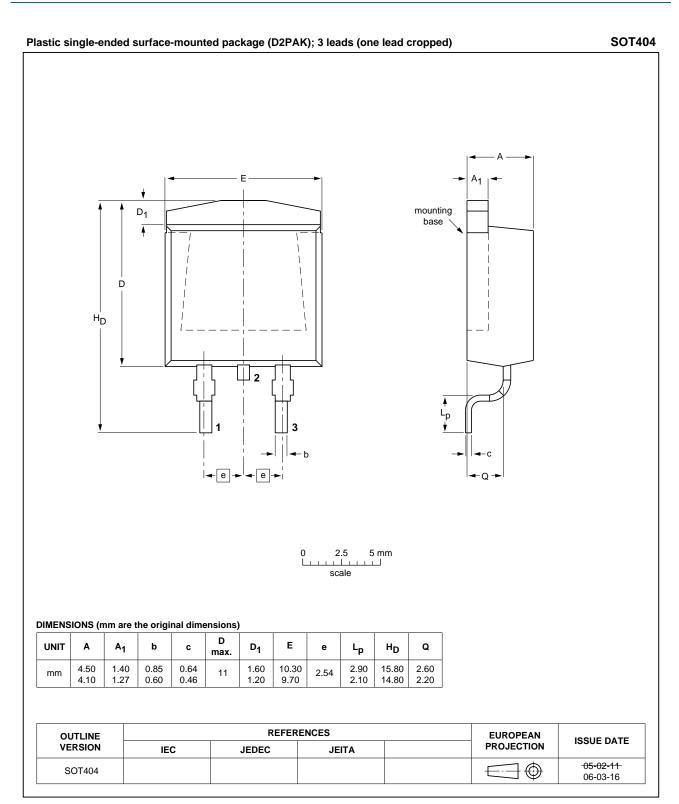


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------------|------------------------------------|--|--------------------|------------------------------|
| PHB45NQ10T v.2 | 20100708 | Product data sheet | - | PHB_PHP_PHW45NQ10T v.1 |
| Modifications: | | this data sheet has been NXP Semiconductors. | en redesigned to o | comply with the new identity |
| | Legal texts ha | ave been adapted to the | new company na | ame where appropriate. |
| | Type number | PHB45NQ10T separate | ed from data shee | t PHB_PHP_PHW45NQ10T v.1. |
| PHB_PHP_PHW45NQ10T v.1 | 19990801 | Product specification | - | - |

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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